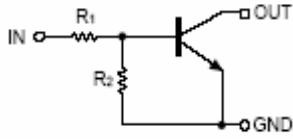


PNP Transistors

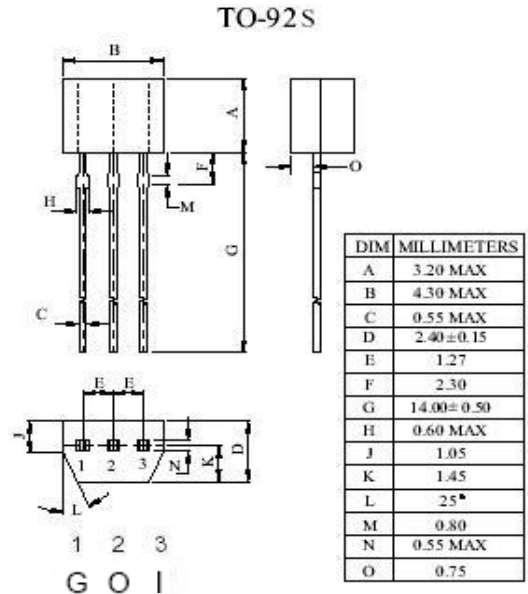
—NPN Silicon—

■■ **APPLICATION:** Interface Circuit and Driver Circuit Applications.



■■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	-10~40	V
Output Current	I_O	30	mA
	$I_{C(Max.)}$	100	mA
Power Dissipation	P_d	0.3	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



■■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Input Voltage	$V_{I(off)}$			0.5	V	$V_{CC}=5V$ $I_O=100\mu A$
	$V_{I(on)}$	3			V	$V_{CC}=0.2V$ $I_O=5mA$
Output Voltage	$V_{O(on)}$		0.1	0.3	V	$I_O=10mA$ $I_I=0.5mA$
Input Current	I_I			0.36	mA	$V_I=5V$
Output Current	$I_{O(off)}$			0.5	uA	$V_{CC}=50V$ $V_I=0V$
DC Current Gain	G_1	56				$V_O=5V$ $I_O=5mA$
Input Resistance	R_1	15.4	22	28.6	KΩ	
Input Resistance	R_2	15.4	22	28.6	KΩ	
Gain bandwidth product	f_T		250		MHz	$V_{CE}=10V$ $I_E=-5mA$ $f=100MHz$

■■ **G_1 Classification And Marking**

Mark	C124ES
Classification	
G_1	≥56